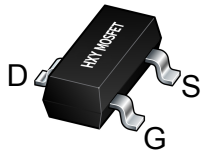
Description

The HXY5N10MI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



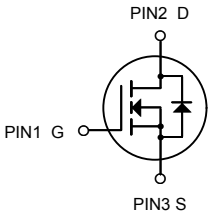
SOT23-3L

General Features

V_{DS} = 100V I_D = 5A

$R_{DS(ON)}$ < 98 mΩ @ V_{GS}=10V

$R_{DS(ON)}$ < 120mΩ @ V_{GS}=4.5V



N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY5N10MI	SOT23-3L	1005	3000

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	100	V
VGS	Gate-Source Voltage	±20	V
I_D	Drain Current-Continuous	5	A
IDM	Drain Current-Pulsed (Note 1)	20	A
P_D	Maximum Power Dissipation	1.5	W
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 175	℃
RθJA	Thermal Resistance,Junction-to-Ambient (Note 2)	100	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1.0	1.5	2.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=3A	-	89	98	mΩ
		V_{GS}=4.5V, I_D=3A	-	102	110	
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=3A	-	5	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V, F=1.0MHz	-	650	-	PF
Output Capacitance	C_{oss}		-	24	-	PF
Reverse Transfer Capacitance	C_{rss}		-	20	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=50V, R_L=19Ω V_{GS}=10V,R_G=3Ω	-	6	-	nS
Turn-on Rise Time	t_r		-	4	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	20	-	nS
Turn-Off Fall Time	t_f		-	4	-	nS
Total Gate Charge	Q_g	V_{DS}=50V,I_D=3A, V_{GS}=10V	-	20		nC
Gate-Source Charge	Q_{gs}		-	2.1	-	nC
Gate-Drain Charge	Q_{gd}		-	3.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=3A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	3	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

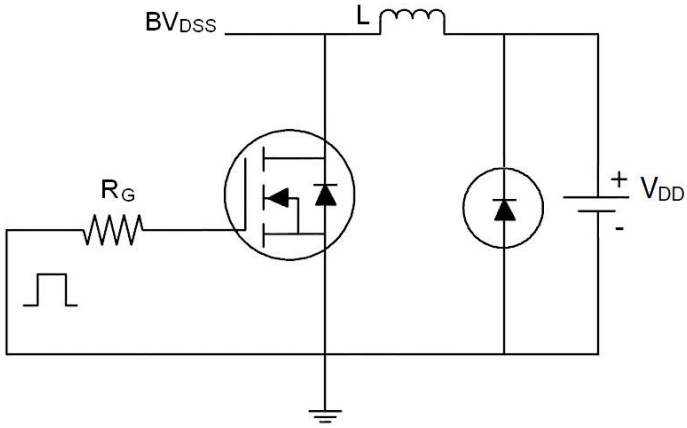
2. Surface Mounted on FR4 Board, t ≤ 10 sec.

3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.

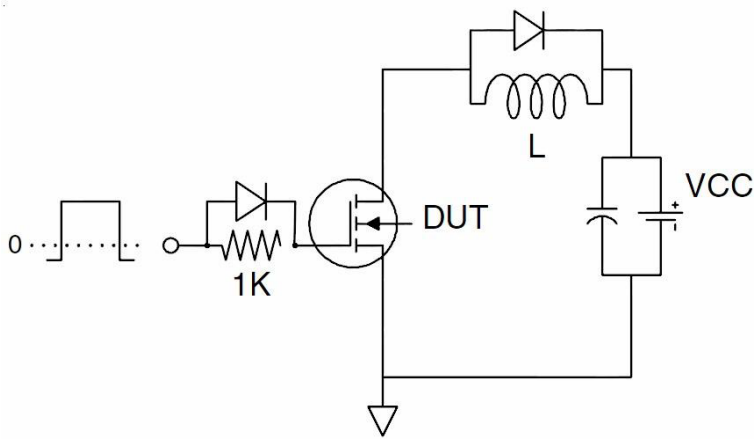
4. Guaranteed by design, not subject to production

Test Circuit

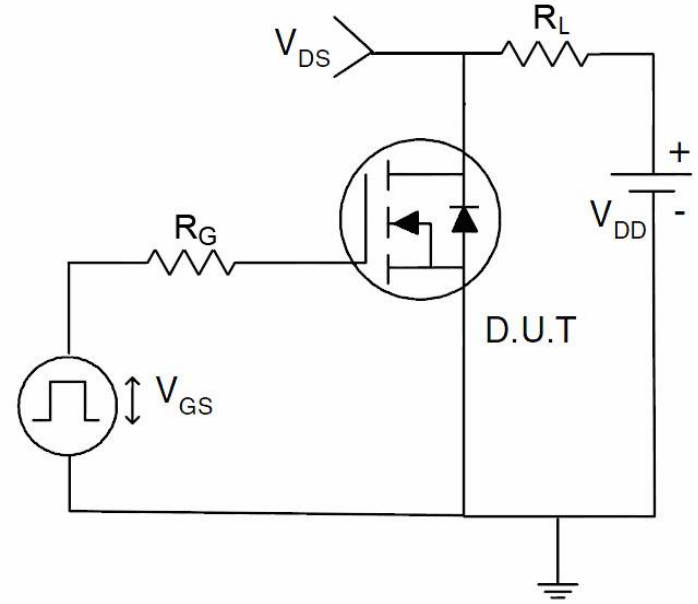
1）E_{AS} test circuit



2）Gate charge test circuit



3）Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

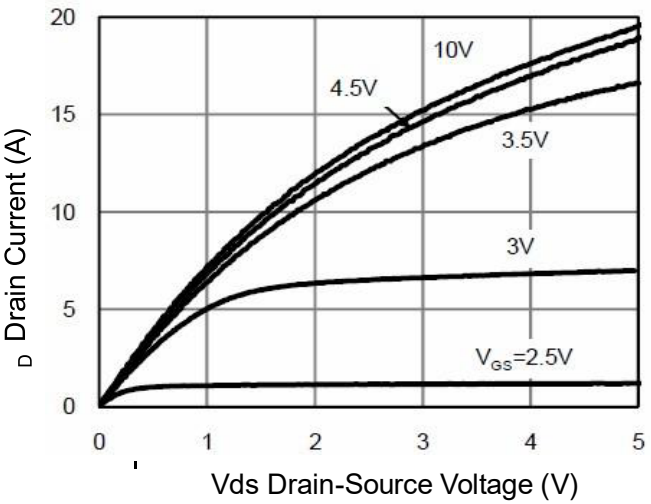


Figure 1 Output Characteristics

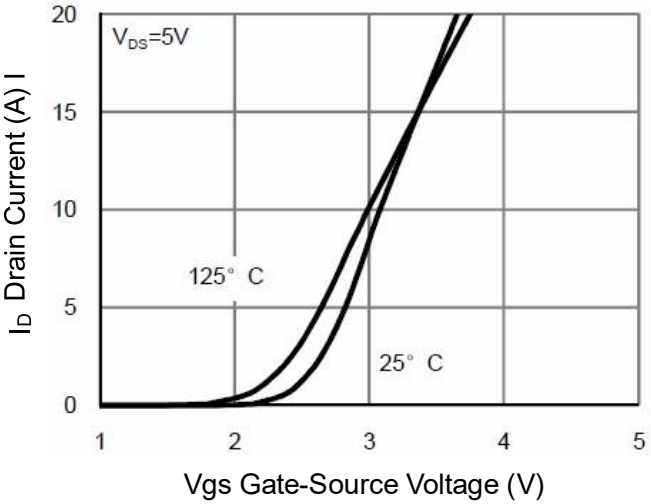


Figure 2 Transfer Characteristics

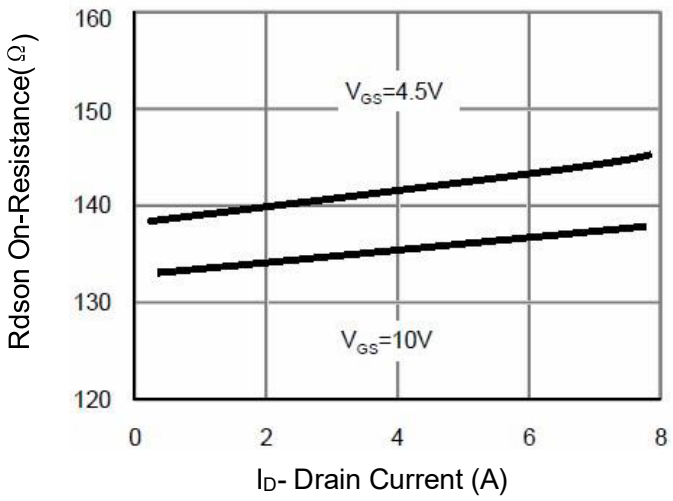


Figure 3 Rdson- Drain Current

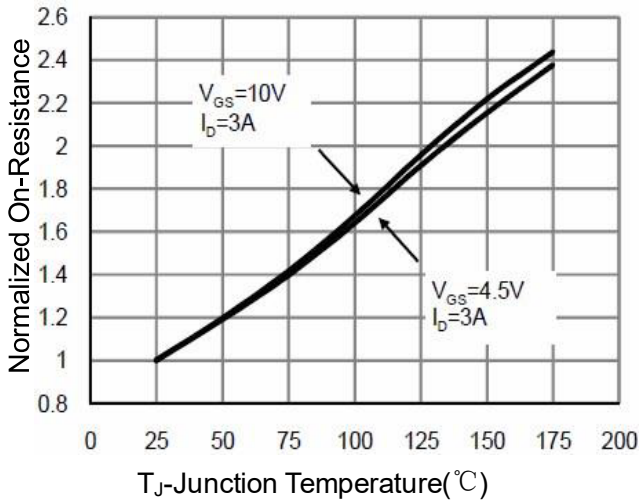


Figure 4 Rdson-JunctionTemperature

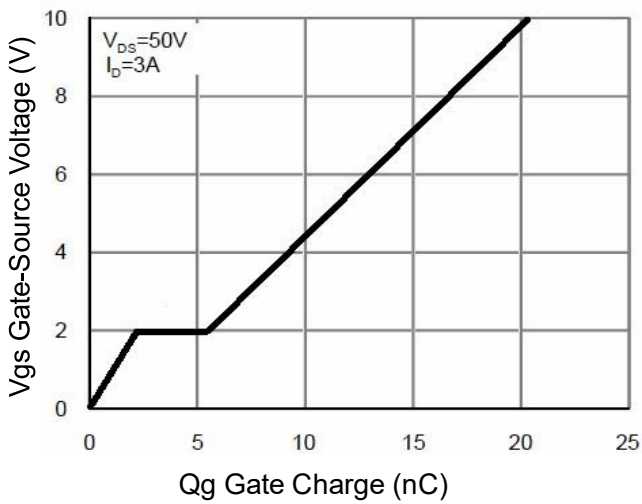


Figure 5 Gate Charge

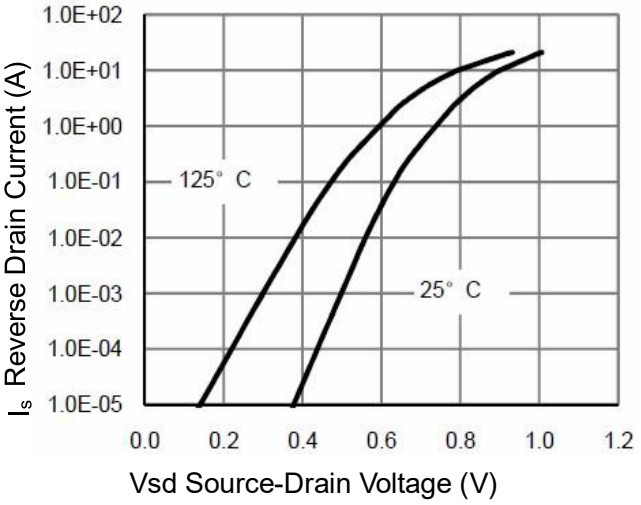


Figure 6 Source- Drain Diode Forward

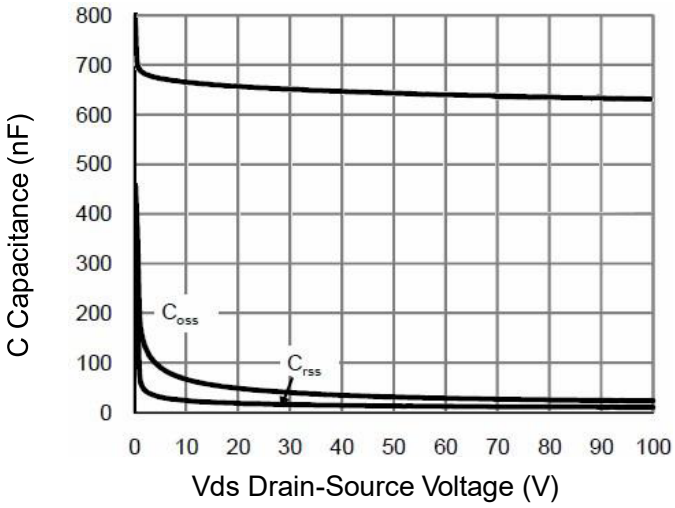


Figure 7 Capacitance vs Vds

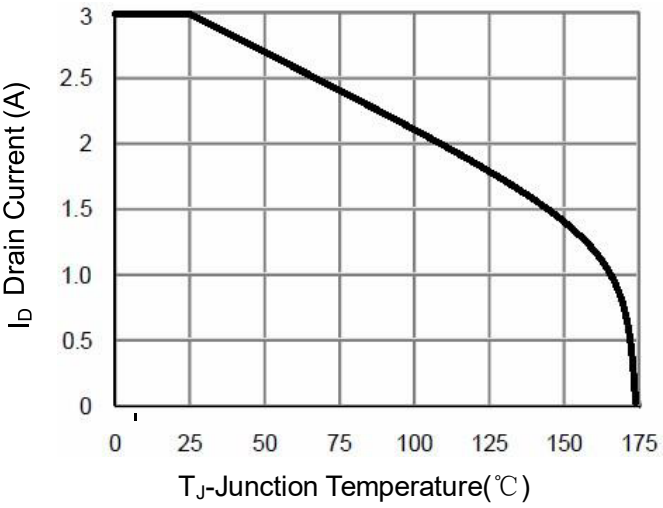


Figure 9 BV_{DSS} vs Junction Temperature

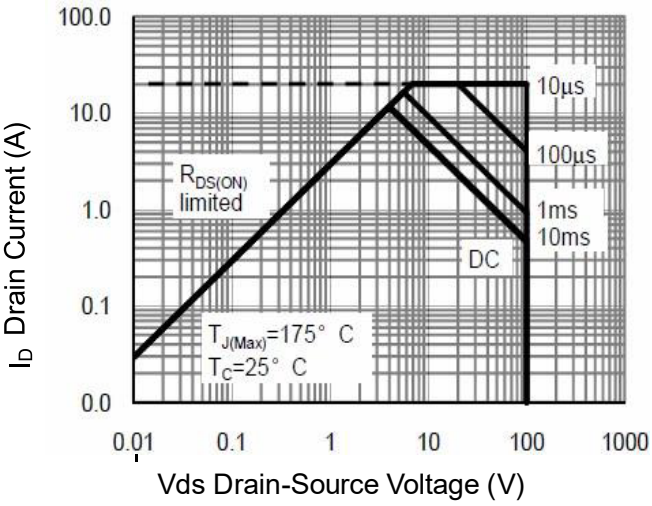


Figure 8 Safe Operation Area

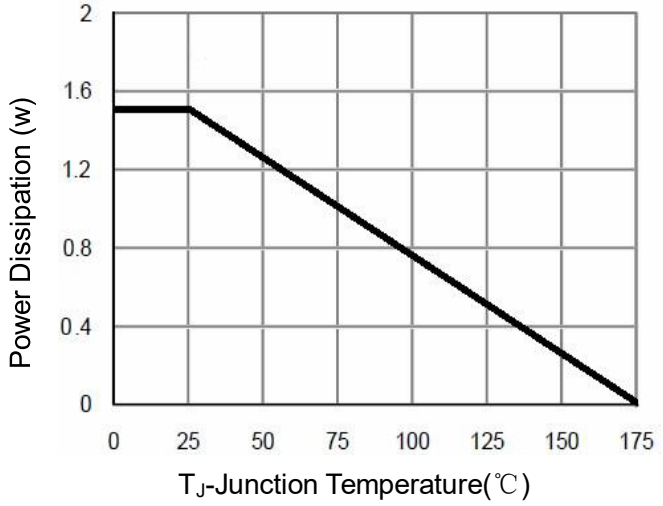


Figure 10 Power De-rating

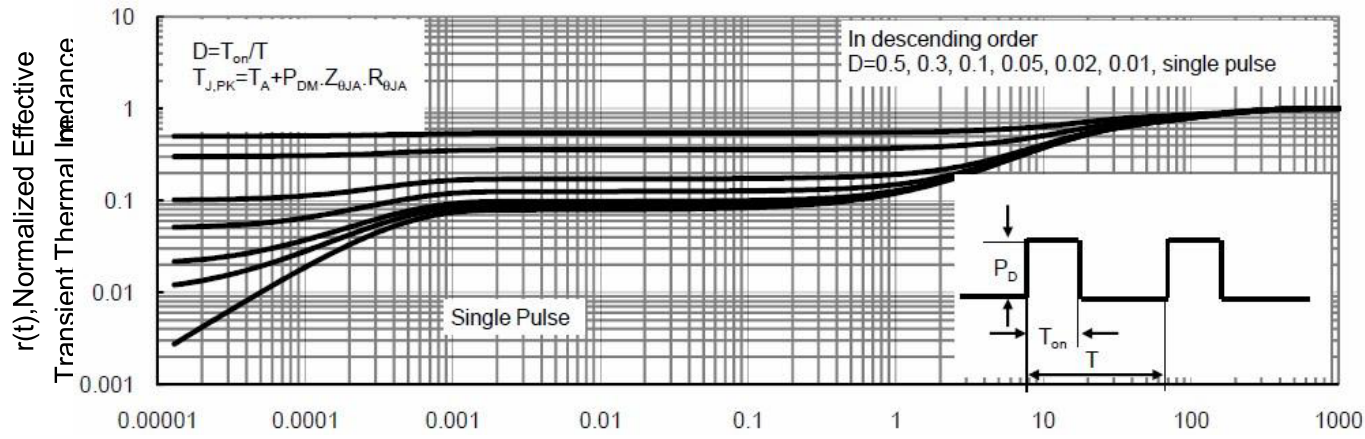
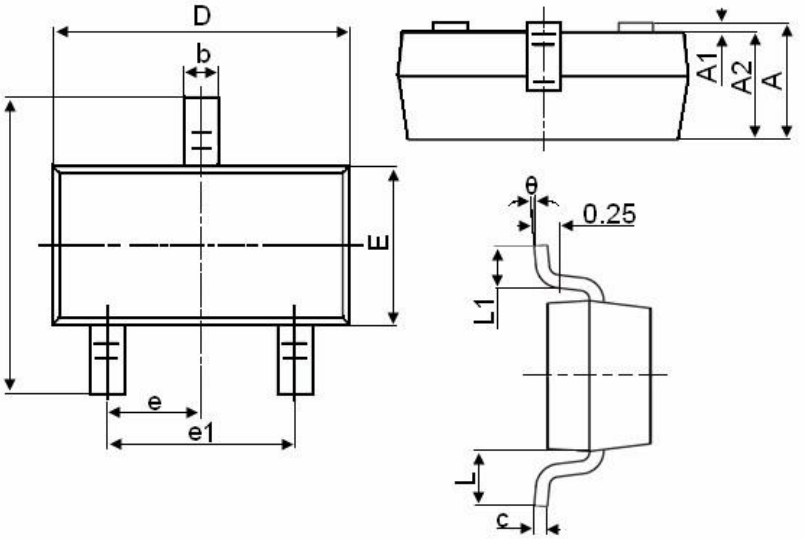


Figure 11 Normalized Maximum Transient Thermal Impedance

SOT23-3L Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°

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